The following listing of claims replaces all prior versions:

Claim 1. (previously presented) A process for electroless copper plating comprising:

1) depositing a palladium on a resin substrate; and

2) treating the resin substrate with a formaldehyde-free electroless copper plating solution, which solution comprises a ~~(i)~~ copper ion~~, and (ii)~~ a reducing agent~~, and (iii) (a) a iodine and/or a water-soluble iodine compound or (b) hydantoin and/or a hydantoin derivative~~, and, wherein no catalyst accelerating treatment is carried out after ~~depositing palladium on the resin substrate performing said catalyst depositing treatment~~.

Claim 2. (currently amended) The process of claim 1 wherein the palladium ~~catalyst~~ is a palladium-tin catalyst.

Claim 3. (previously presented) The process for electroless copper plating according to claim 1 wherein the electroless copper plating solution further comprises a complexing agent.

Claim 4. (currently amended) The process for electroless copper plating according to claim 1 wherein the reducing agent is selected from a group consisting of sodium boron hydride, potassium boron hydride, dimethylamino borane, trimethylamino borane, ~~hydrazine, derivatives of these compounds and a mixture~~ mixtures thereof.

Claim 5. (previously presented) The process for electroless copper plating according to claim 1, wherein the electroless copper plating solution further comprises a water-soluble cerium compound, a water-soluble thallium and/or a water-soluble sulfide.

Claim 6. (currently amended) The process for electroless copper plating according to claim 1, wherein the electroless copper plating solution ~~further~~ comprises iodine and/or a water-soluble iodine compound.

Claim 7. (currently amended) The process for electroless copper plating according to claim 1, wherein the electroless copper plating solution ~~further~~ comprises hydantoin and/or a hydantoin derivative.

Claim 8. (previously presented) The process for electroless copper plating according to claim 1, wherein the deposition rate of copper is 0.05 micrometer/minute or more.

Claim 9. (previously presented) An electroless copper plating solution used in the process for electroless copper plating according to claim 1.

Claim 10. (previously presented) An electroless plating system, comprising a resin substrate disposed in a plating solution of claim 9.

Claim 11. (previously presented) A composite material prepared by the process according to claim 1.

Claim 12. (previously presented) The composite material according to claim 11, wherein the thickness of the copper layer deposited on the resin substrate is 0.05 micrometer or more.

Claim 13. (previously presented) A process for electro plating copper characterized by further applying an electro copper plating on the composite material according to claim 11.

Claim 14. (previously presented) A composite material prepared by the process in accordance with claim 13.

Claim 15. (new) The process of claim 6 wherein the plating solution comprises potassium iodide, ammonium iodide, or an organic compound comprising covalent bound iodine.

Claim 16. (new) The process of claim 6 wherein the plating solution comprises thallium iodide in combination with a distinct water-soluble iodine compound.

Claim 17. (new) The process of claim 1 wherein the plating solution comprises (a) a iodine and/or a water-soluble iodine compound and (b) hydantoin and/or a hydantoin derivative.